78.(New) The device of claim 1 wherein said channel-forming region has point defects.

F3 cont.

79.(New) The device of claim 2 wherein said channel-forming region has point defects.

80.(New) The device of claim 3 wherein said channel-forming region has point defects.

81.(New) The device of claim 8 wherein said channel-forming region has point defects.

82.(New) A central processing unit comprising:

a thin film transistor on an insulating surface, said thin film transistor comprising:

a semiconductor layer having at least a pair of source and drain regions, and a channel-forming region interposed therebetween; and

a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said channel-forming region contains carbon and nitrogen at a concentration of 5×10^{18} cm^{-3} or less, and oxygen at a concentration of 5×10^{19} cm^{-3} or less, and

wherein said channel-forming region does not have linear defects or surface defects.

83.(New) The device of claim 82 wherein at least said channel-forming region is provided in a region which can be regarded as being effectively monocrystalline, and wherein said region which can be regarded as being effectively monocrystalline comprises silicon.

F3 cont.

84.(New) The device of claim 83 wherein ratio (W/W_0) between width W_0 of a spectrum at a position at half of a Raman spectrum intensity for a monocrystalline silicon wafer and a width W of a spectrum at a position at half of a Raman spectrum intensity for said regions which can be regarded as being effectively monocrystalline is 2.0 or less.

85.(New) The device of claim 83 wherein ratio (I/I_0) between a Raman spectrum intensity I_0 of a monocrystalline silicon wafer and a Raman spectrum intensity I of said regions which can be regarded as being effectively monocrystalline is 0.8 or more.

86.(New) The device of claim 82 wherein said channel-forming region has point defects.

87.(New) The device of claim 82 wherein said central processing unit is incorporated in a display device.

88.(New) A memory comprising:

a thin film transistor on an insulating surface, said thin film transistor comprising:

a semiconductor layer having at least a pair of source and drain regions, and a channel-forming region interposed therebetween; and

a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said channel-forming region contains carbon and nitrogen at a concentration of 5×10^{18} cm^{-3} or less, and oxygen at a concentration of 5×10^{19} cm-3 or less, and

wherein said channel-forming region does not have linear defects or surface defects.

F3 cont.

89.(New) The device of claim 88 wherein at least said channel-forming region is provided in a region which can be regarded as being effectively monocrystalline, and wherein said region which can be regarded as being effectively monocrystalline comprises silicon.

90.(New) The device of claim 89 wherein ratio (W/W_o) between width W_o of a spectrum at a position at half of a Raman spectrum intensity for a monocrystalline silicon wafer and a width W of a spectrum at a position at half of a Raman spectrum intensity for said regions which can be regarded as being effectively monocrystalline is 2.0 or less.

91.(New) The device of claim 89 wherein ratio (I/I_o) between a Raman spectrum intensity I_o of a monocrystalline silicon wafer and a Raman spectrum intensity I of said regions which can be regarded as being effectively monocrystalline is 0.8 or more.

92.(New) The device of claim 88 wherein said channel-forming region has point defects.

93.(New) The device of claim 88 wherein said memory is incorporated in a display device.

94.(New) An input port comprising:

a thin film transistor on an insulating surface, said thin film transistor comprising:

a semiconductor layer having at least a pair of source and drain regions, and a channel-forming region interposed therebetween; and

a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said channel-forming region contains carbon and nitrogen at a concentration of 5×10^{18} cm^{-3} or less, and oxygen at a concentration of 5×10^{19} cm^{-3} or less, and

wherein said channel-forming region does not have linear defects or surface defects.

95.(New) The device of claim 94 wherein at least said channel-forming region is provided in a region which can be regarded as being effectively monocrystalline, and wherein said region which can be regarded as being effectively monocrystalline comprises silicon.

96.(New) The device of claim 95 wherein ratio (W/W_o) between width W_o of a spectrum at a position at half of a Raman spectrum intensity for a monocrystalline silicon wafer and a width W of a spectrum at a position at half of a Raman spectrum intensity for said regions which can be regarded as being effectively monocrystalline is 2.0 or less.

97.(New) The device of claim 95 wherein ratio (I/I_o) between a Raman spectrum intensity I_o of a monocrystalline silicon wafer and a Raman spectrum intensity I of said regions which can be regarded as being effectively monocrystalline is 0.8 or more.

98.(New) The device of claim 94 wherein said channel-forming region has point defects.

F3 Concl'd

99.(New) The device of claim 94 wherein said input port is incorporated in a display device.